

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 150\mu A$ ④	CT6
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.30	—	V/°C	$V_{GE} = 0V, I_C = 1mA (25^\circ\text{C}-175^\circ\text{C})$	CT6
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.65	2.14	V	$I_C = 48A, V_{GE} = 15V, T_J = 25^\circ\text{C}$	5, 6, 7
		—	2.0	—		$I_C = 48A, V_{GE} = 15V, T_J = 150^\circ\text{C}$	9, 10, 11
		—	2.05	—		$I_C = 48A, V_{GE} = 15V, T_J = 175^\circ\text{C}$	
$V_{GE(th)}$	Gate Threshold Voltage	4.0	—	6.5	V	$V_{CE} = V_{GE}, I_C = 1.4mA$	9, 10,
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-21	—	mV/°C	$V_{CE} = V_{GE}, I_C = 1.0mA (25^\circ\text{C} - 175^\circ\text{C})$	11, 12
g_{fe}	Forward Transconductance	—	32	—	S	$V_{CE} = 50V, I_C = 48A, PW = 80\mu s$	
I_{CES}	Collector-to-Emitter Leakage Current	—	1.0	150	μA	$V_{GE} = 0V, V_{CE} = 600V$	
		—	450	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 175^\circ\text{C}$	
V_{FM}	Diode Forward Voltage Drop	—	1.95	2.91	V	$I_F = 48A$	8
		—	1.45	—		$I_F = 48A, T_J = 175^\circ\text{C}$	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$	

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig
Q_g	Total Gate Charge (turn-on)	—	95	140	nC	$I_C = 48A$	24
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	28	42		$V_{GE} = 15V$	CT1
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	35	53		$V_{CC} = 400V$	
E_{on}	Turn-On Switching Loss	—	625	1141	μJ	$I_C = 48A, V_{CC} = 400V, V_{GE} = 15V$	CT4
E_{off}	Turn-Off Switching Loss	—	1275	1481		$R_G = 10\Omega, L = 200\mu H, L_S = 150nH, T_J = 25^\circ\text{C}$	
E_{total}	Total Switching Loss	—	1900	2622		Energy losses include tail & diode reverse recovery	
$t_{d(on)}$	Turn-On delay time	—	60	78	ns	$I_C = 48A, V_{CC} = 400V, V_{GE} = 15V$	CT4
t_r	Rise time	—	40	56		$R_G = 10\Omega, L = 200\mu H, L_S = 150nH, T_J = 25^\circ\text{C}$	
$t_{d(off)}$	Turn-Off delay time	—	145	176			
t_f	Fall time	—	35	46	μJ	$I_C = 48A, V_{CC} = 400V, V_{GE} = 15V$	13, 15
E_{on}	Turn-On Switching Loss	—	1625	—		$R_G = 10\Omega, L = 200\mu H, L_S = 150nH, T_J = 175^\circ\text{C}$ ④	CT4
E_{off}	Turn-Off Switching Loss	—	1585	—		Energy losses include tail & diode reverse recovery	WF1, WF2
E_{total}	Total Switching Loss	—	3210	—	ns	$I_C = 48A, V_{CC} = 400V, V_{GE} = 15V$	14, 16
$t_{d(on)}$	Turn-On delay time	—	55	—		$R_G = 10\Omega, L = 200\mu H, L_S = 150nH$	CT4
t_r	Rise time	—	45	—		$T_J = 175^\circ\text{C}$	WF1
$t_{d(off)}$	Turn-Off delay time	—	165	—	pF		WF2
t_f	Fall time	—	45	—			
C_{ies}	Input Capacitance	—	3025	—		$V_{GE} = 0V$	23
C_{oes}	Output Capacitance	—	245	—		$V_{CC} = 30V$	
C_{res}	Reverse Transfer Capacitance	—	90	—		$f = 1.0Mhz$	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 175^\circ\text{C}, I_C = 192A$ $V_{CC} = 480V, V_p = 600V$ $R_g = 10\Omega, V_{GE} = +15V \text{ to } 0V$	4 CT2
SCSOA	Short Circuit Safe Operating Area	5	—	—	μs	$V_{CC} = 400V, V_p = 600V$ $R_g = 10\Omega, V_{GE} = +15V \text{ to } 0V$	22, CT3 WF4
E_{rec}	Reverse Recovery Energy of the Diode	—	845	—	μJ	$T_J = 175^\circ\text{C}$	17, 18, 19
t_{rr}	Diode Reverse Recovery Time	—	115	—	ns	$V_{CC} = 400V, I_F = 48A$	20, 21
I_{rr}	Peak Reverse Recovery Current	—	40	—	A	$V_{GE} = 15V, R_g = 10\Omega, L = 200\mu H, L_s = 150nH$	WF3

Notes:

- ① $V_{CC} = 80\% (V_{CES}), V_{GE} = 20V, L = 200\mu H, R_G = 10\Omega$.
- ② This is only applied to TO-247AC package.
- ③ Pulse width limited by max. junction temperature.
- ④ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.

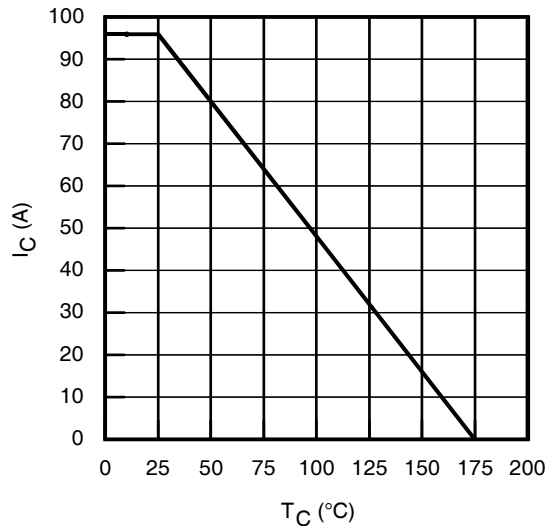


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

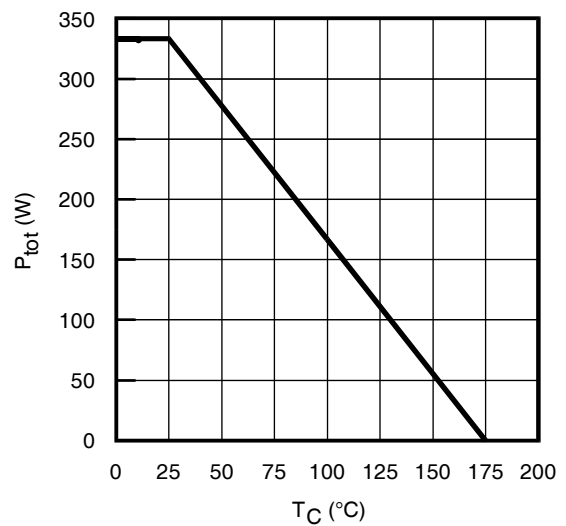


Fig. 2 - Power Dissipation vs. Case Temperature

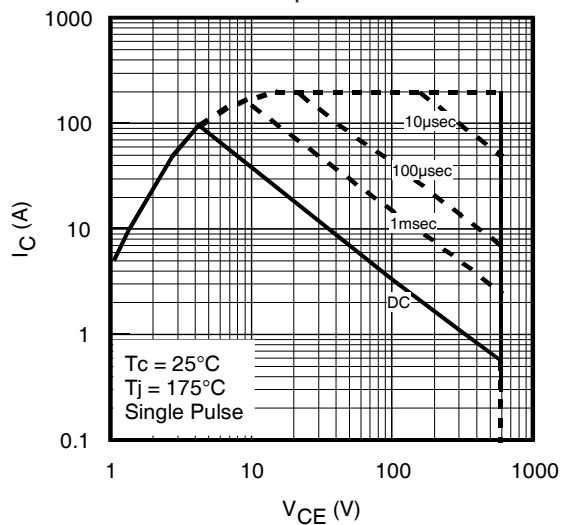


Fig. 3 - Forward SOA
 $T_C = 25^\circ\text{C}$, $T_J \leq 175^\circ\text{C}$; $V_{GE} = 15\text{V}$

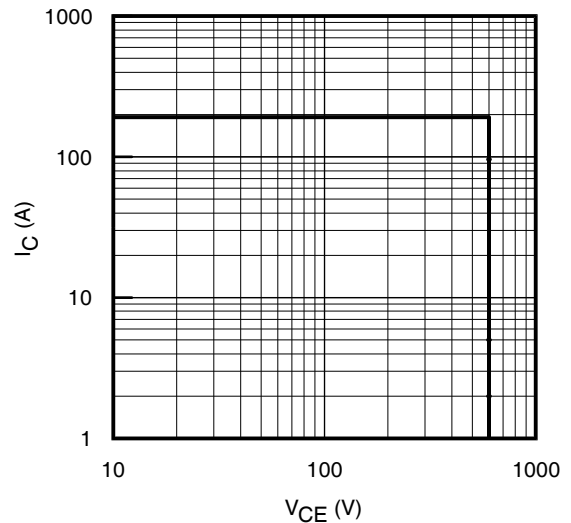


Fig. 4 - Reverse Bias SOA
 $T_J = 175^\circ\text{C}$; $V_{GE} = 15\text{V}$

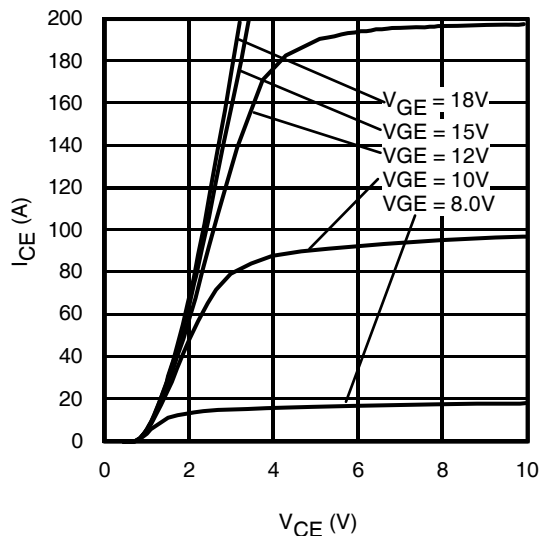


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^\circ\text{C}$; $t_p = 80\mu\text{s}$

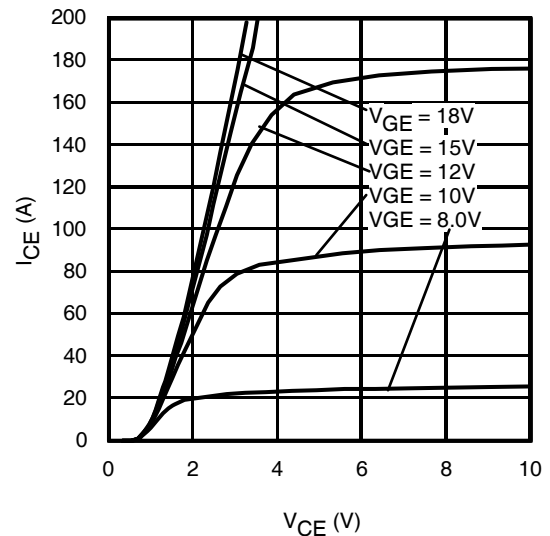


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 80\mu\text{s}$

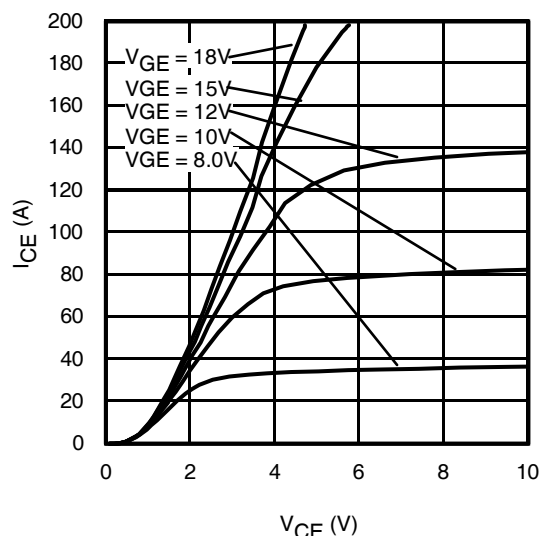


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 175^\circ\text{C}$; $t_p = 80\mu\text{s}$

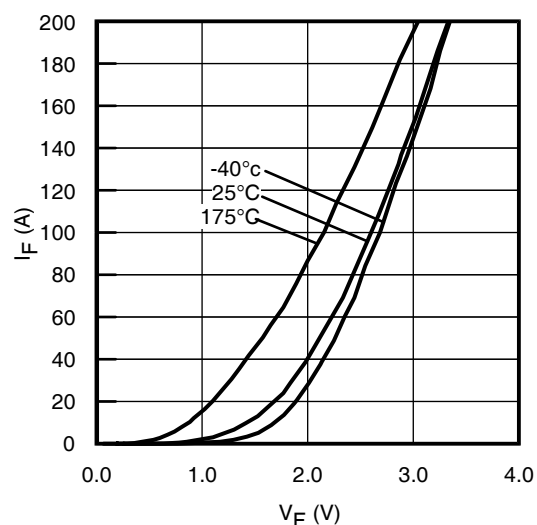


Fig. 8 - Typ. Diode Forward Characteristics
 $t_p = 80\mu\text{s}$

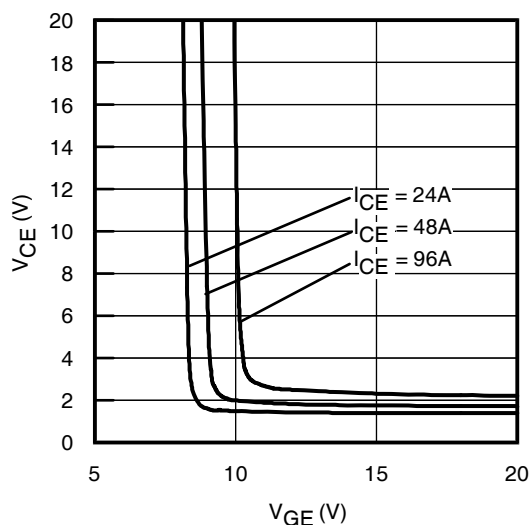


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

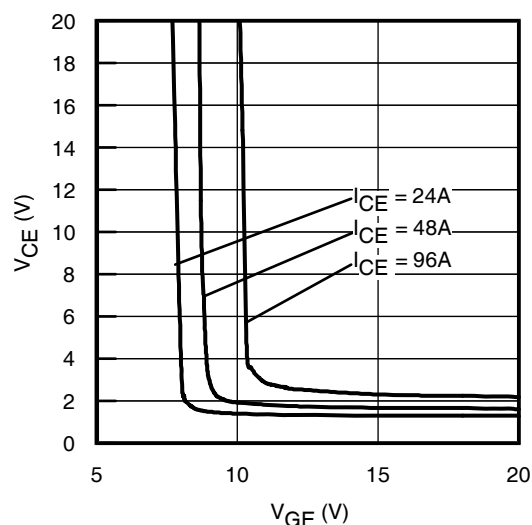


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

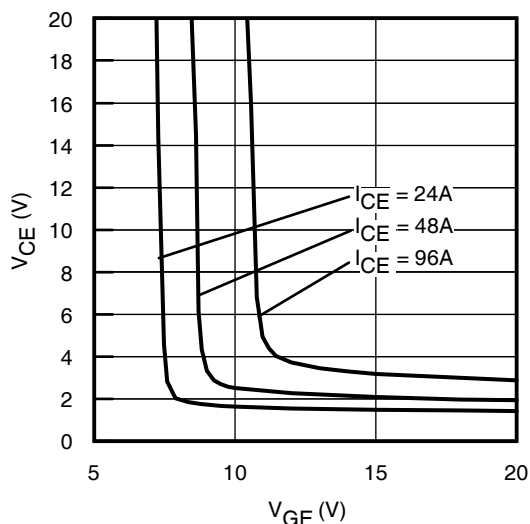


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 175^\circ\text{C}$

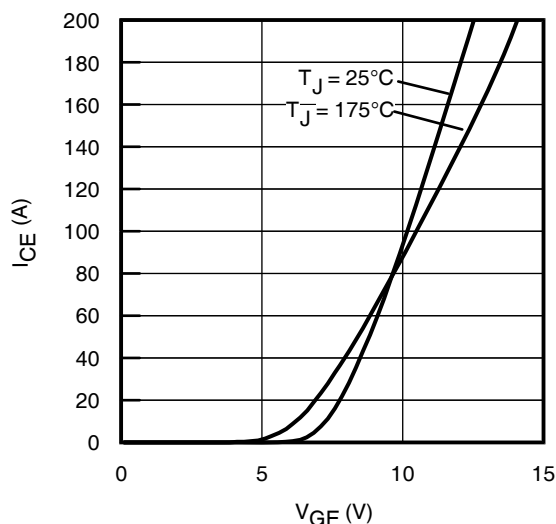


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 10\mu\text{s}$

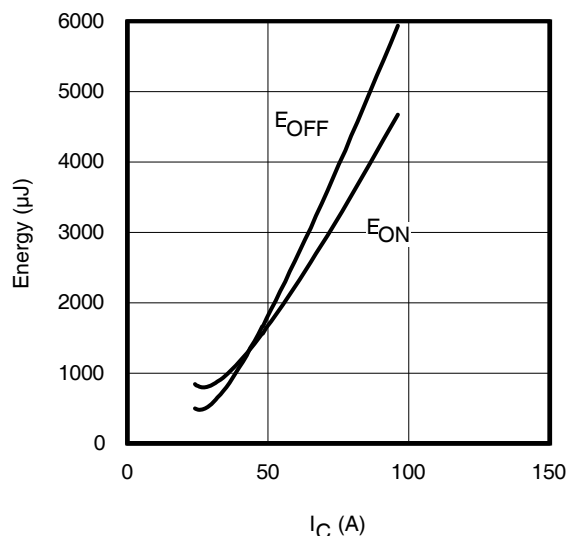


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 400\text{V}$; $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

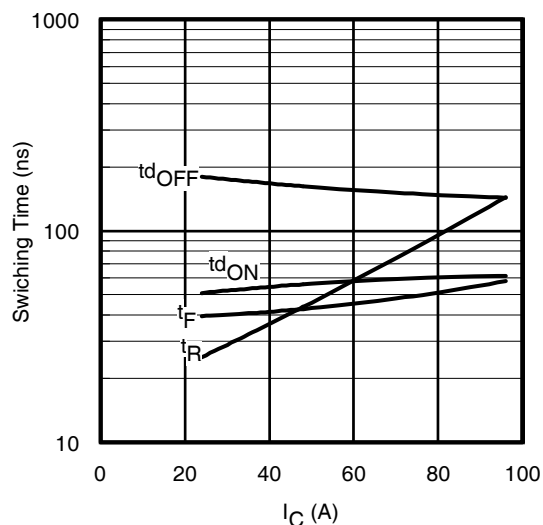


Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 400\text{V}$; $R_G = 10\Omega$; $V_{GE} = 15\text{V}$

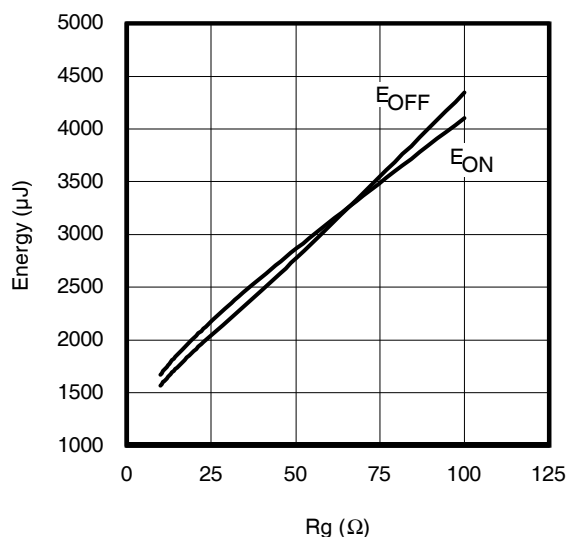


Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 400\text{V}$; $I_{CE} = 48\text{A}$; $V_{GE} = 15\text{V}$

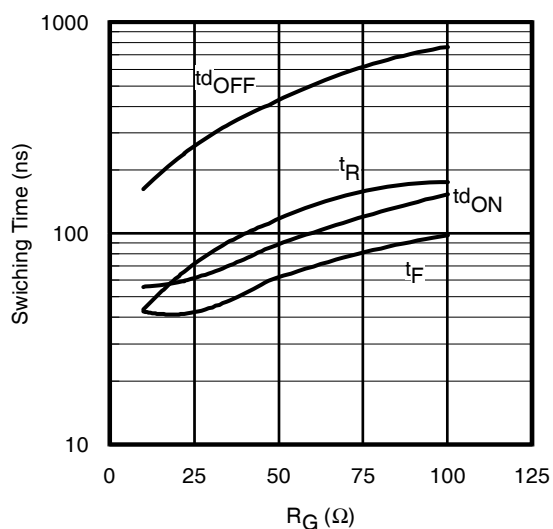


Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 175^\circ\text{C}$; $L = 200\mu\text{H}$; $V_{CE} = 400\text{V}$; $I_{CE} = 48\text{A}$; $V_{GE} = 15\text{V}$

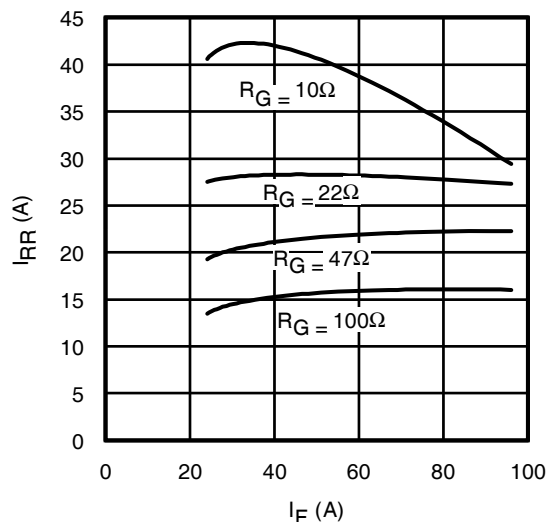


Fig. 17 - Typ. Diode I_{RR} vs. I_F
 $T_J = 175^\circ\text{C}$

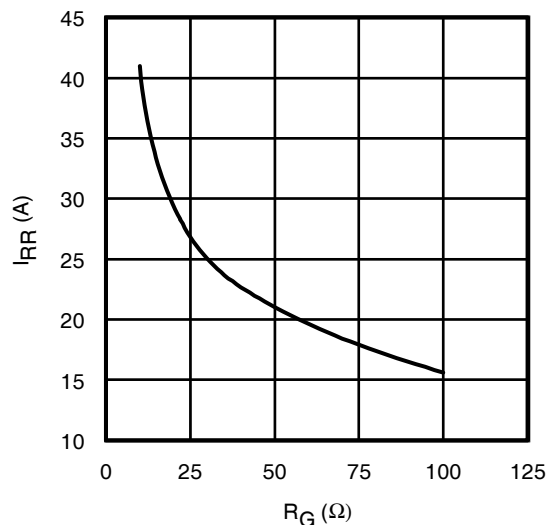


Fig. 18 - Typ. Diode I_{RR} vs. R_G
 $T_J = 175^\circ\text{C}$

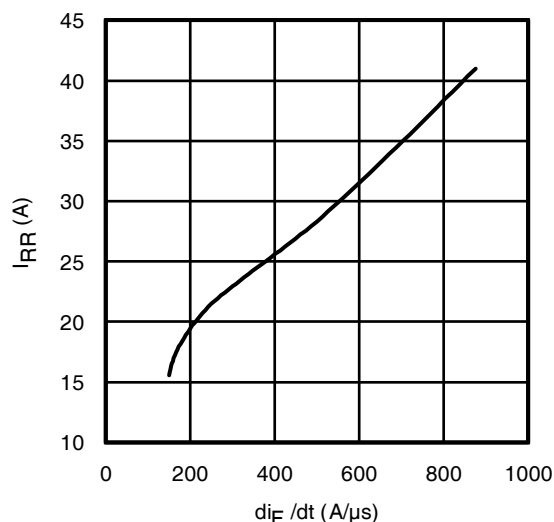


Fig. 19 - Typ. Diode I_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $I_F = 48A$; $T_J = 175^\circ C$

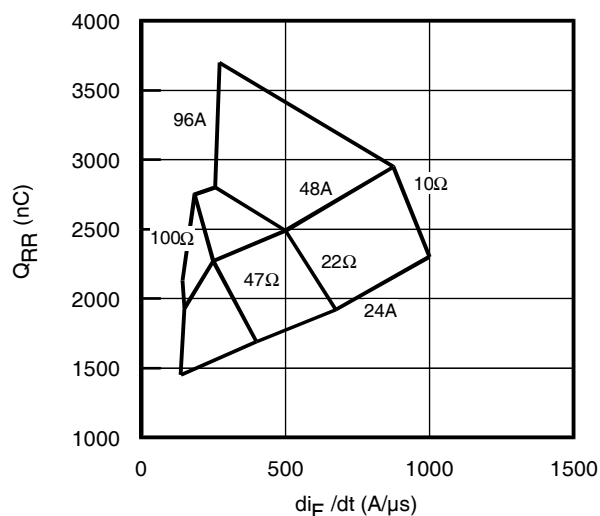


Fig. 20 - Typ. Diode Q_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $T_J = 175^\circ C$

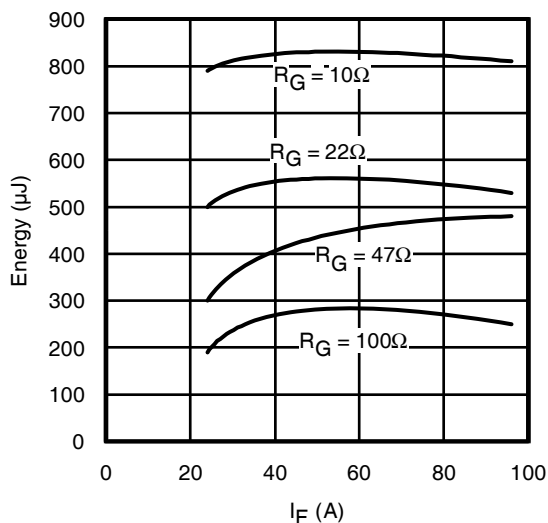


Fig. 21 - Typ. Diode E_{RR} vs. I_F
 $T_J = 175^\circ C$

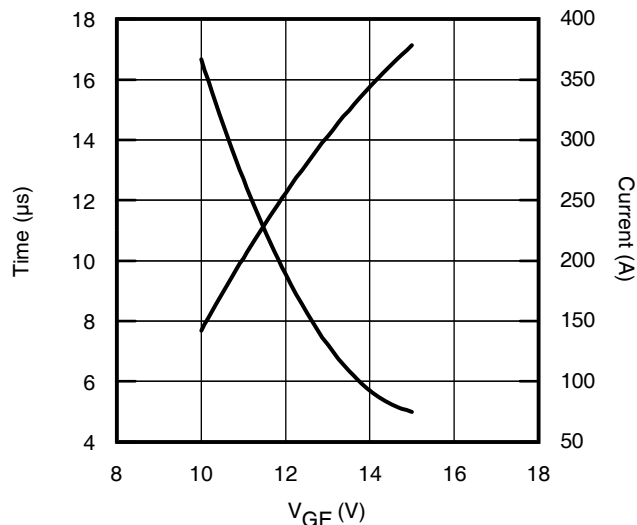


Fig. 22 - V_{GE} vs. Short Circuit Time
 $V_{CC} = 400V$; $T_C = 25^\circ C$

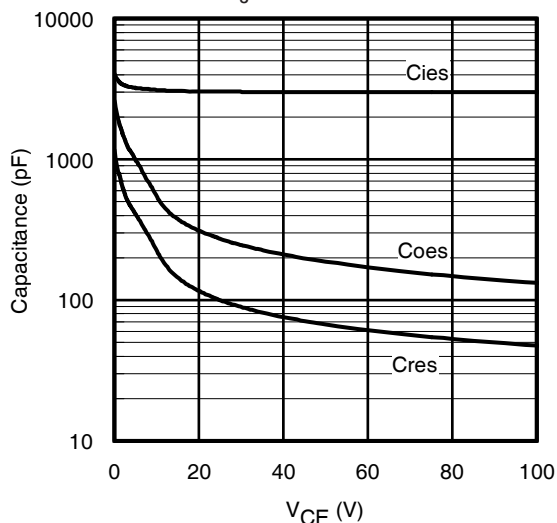


Fig. 23 - Typ. Capacitance vs. V_{CE}

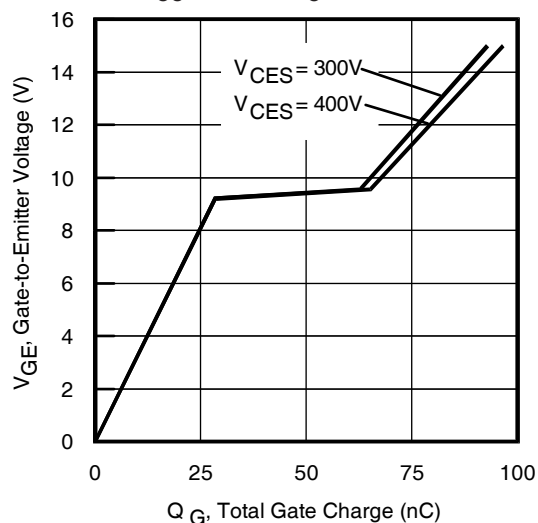


Fig. 24 - Typical Gate Charge vs. V_{GE}

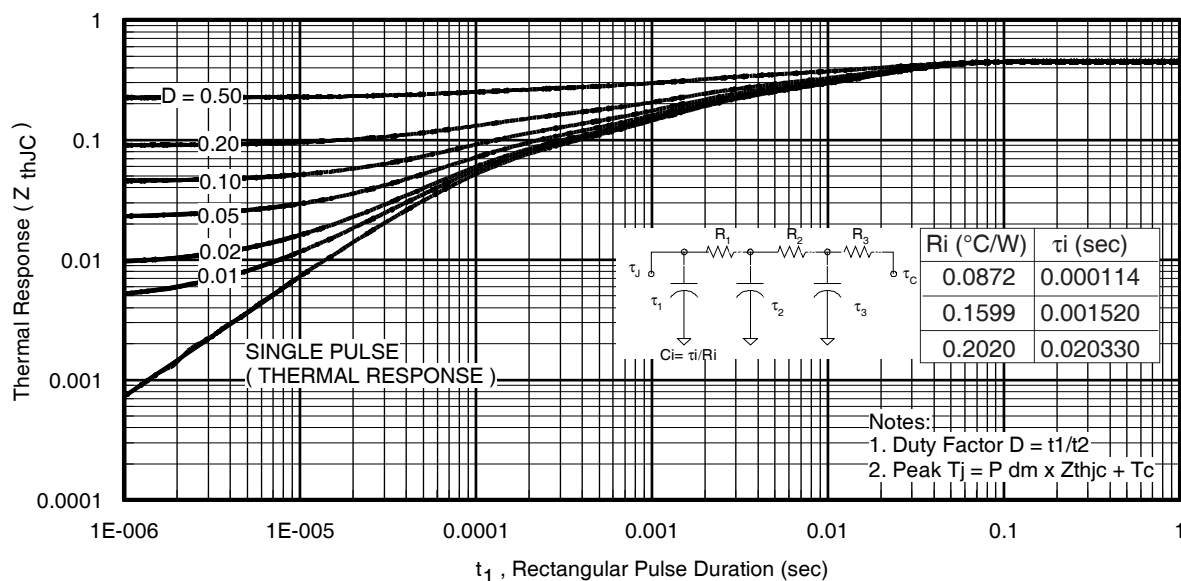


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

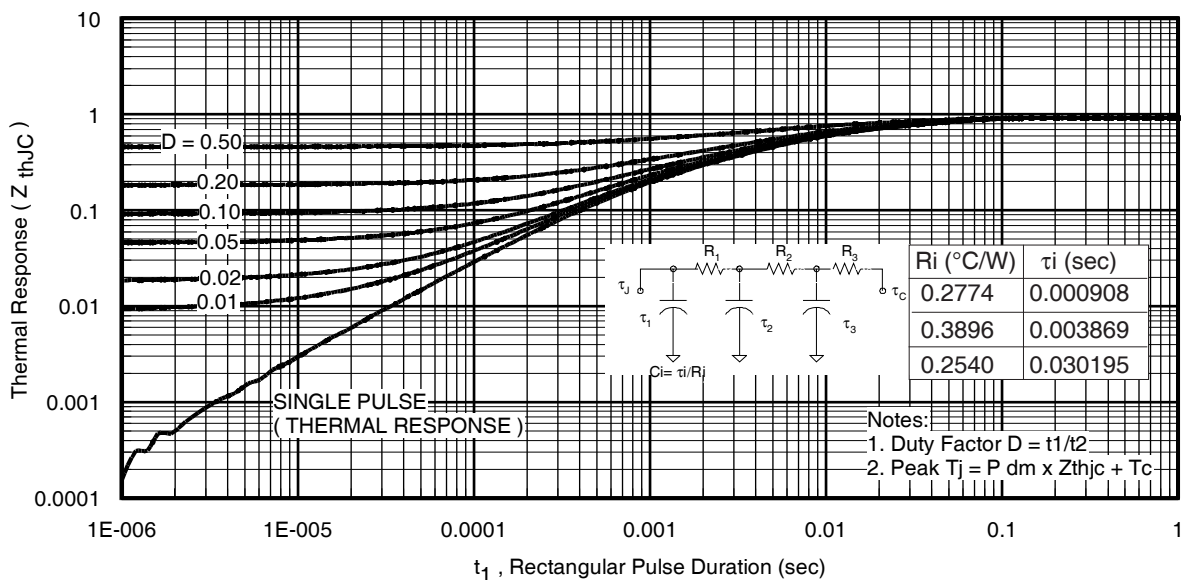
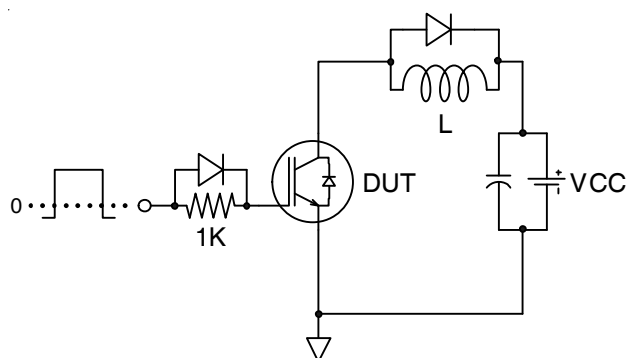
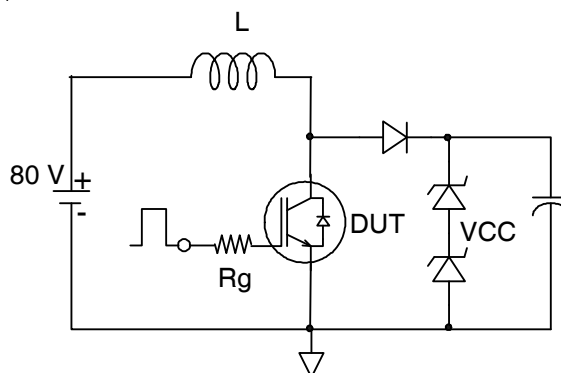
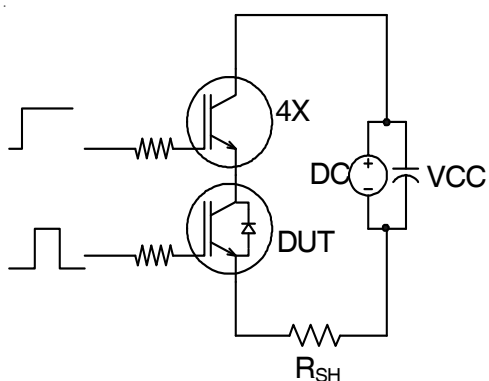
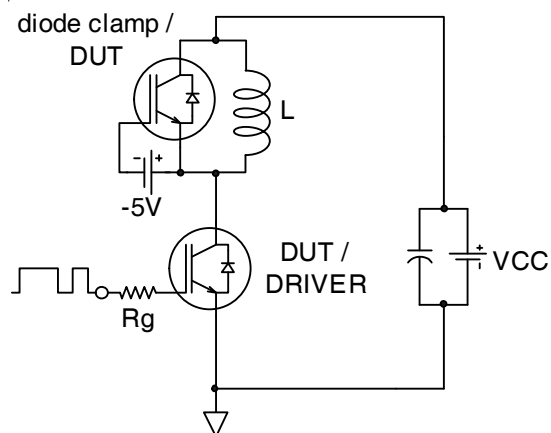
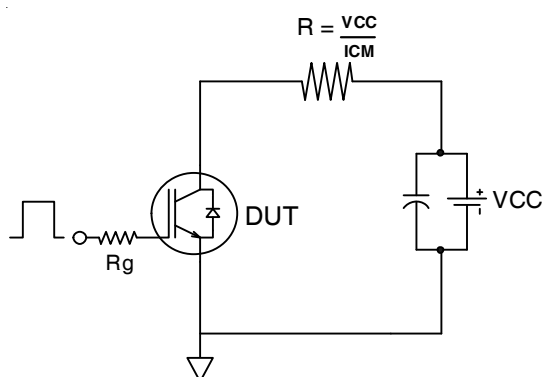
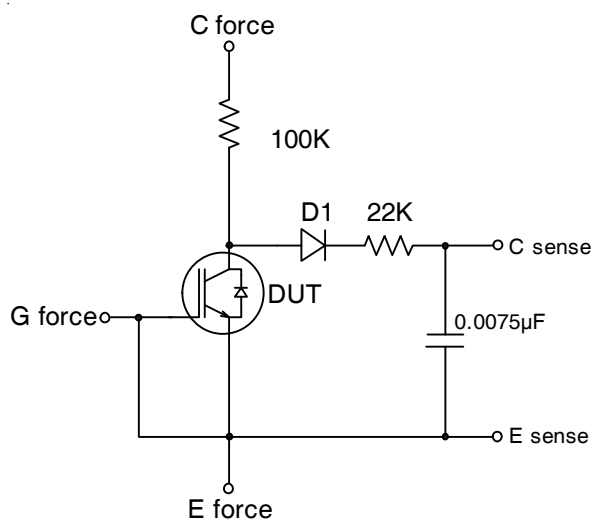


Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)


Fig.C.T.1 - Gate Charge Circuit (turn-off)

Fig.C.T.2 - RBSOA Circuit

Fig.C.T.3 - S.C. SOA Circuit

Fig.C.T.4 - Switching Loss Circuit

Fig.C.T.5 - Resistive Load Circuit

Fig.C.T.6 - BVCES Filter Circuit

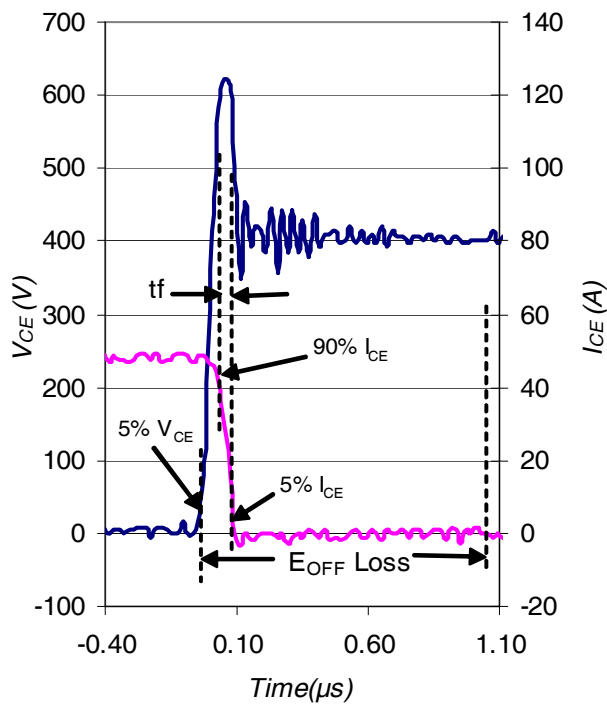


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

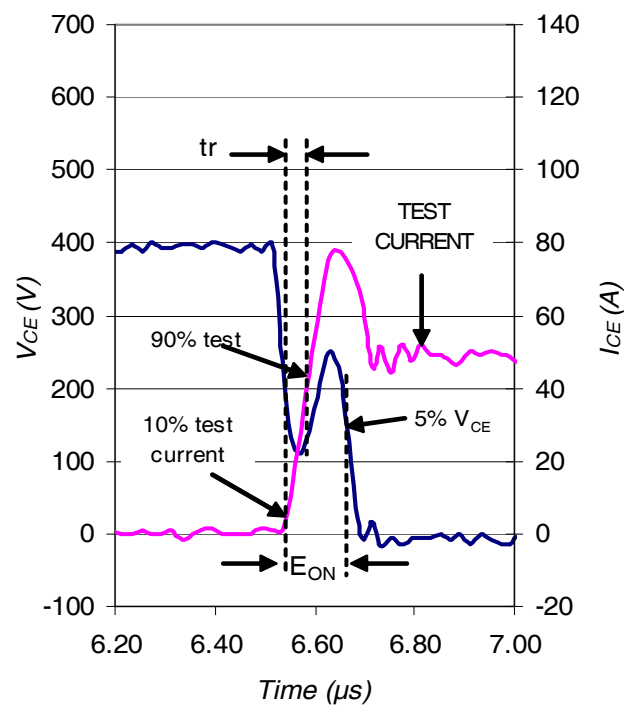


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

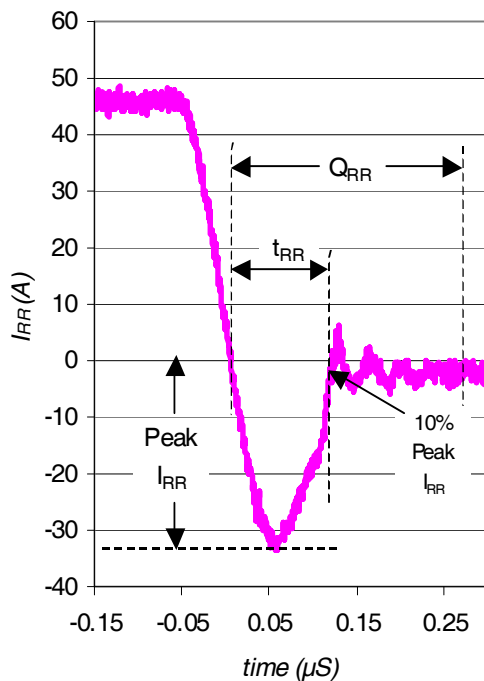


Fig. WF3 - Typ. Diode Recovery Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

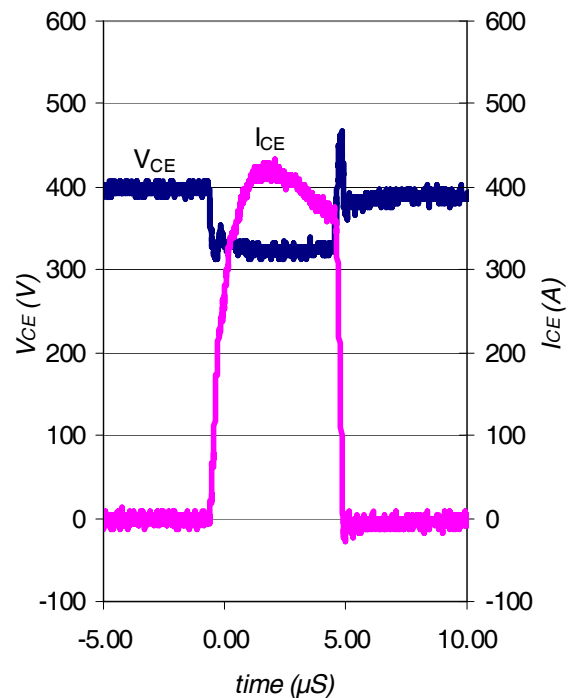
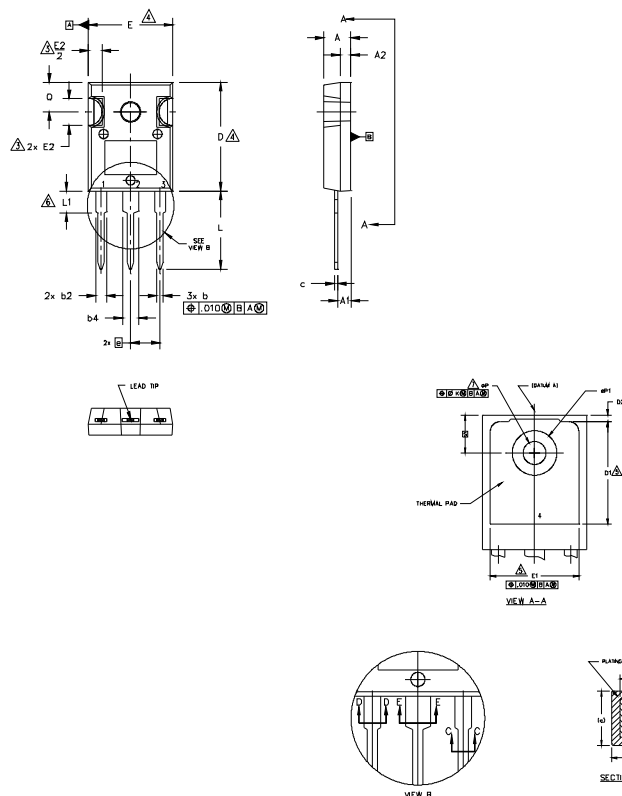


Fig. WF4 - Typ. S.C. Waveform
@ $T_J = 25^\circ\text{C}$ using Fig. CT.3

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH; MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	—	13.08	—	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

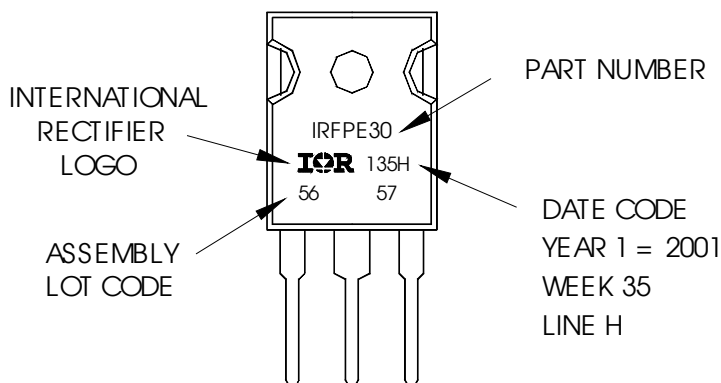
DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2001
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position
indicates "Lead-Free"

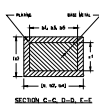
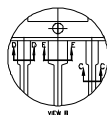
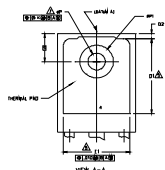
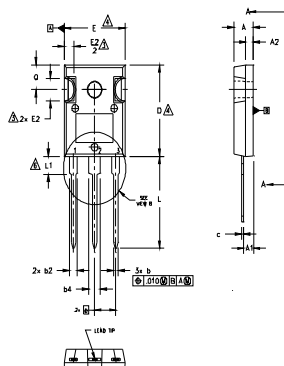


TO-247AC package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

TO-247AD Package Outline

Dimensions are shown in millimeters (inches)



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- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
- LEAD FINISH UNCONTROLLED IN LT.
- ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
- OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

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b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	-	13.46	-	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øe	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	-	.291	-	7.39	
D	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- GATE
- DRAIN
- SOURCE
- DRAIN

IGBTs, CoPACK

- GATE
- COLLECTOR
- EMITTER
- COLLECTOR

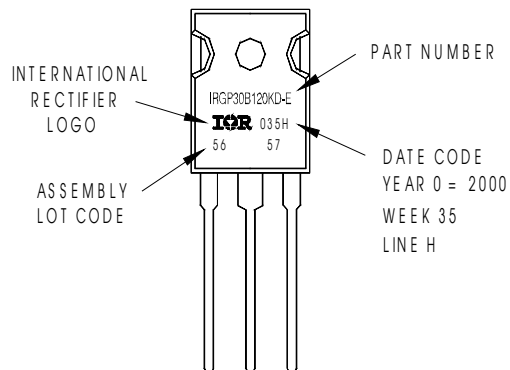
DIODES

- ANODE/OPEN
- CATHODE
- ANODE

TO-247AD Part Marking Information

EXAMPLE: THIS IS AN IRGP30B120KD-E
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position
indicates "Lead-Free"



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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